

2SC5545

Silicon NPN Epitaxial
VHF / UHF wide band amplifier

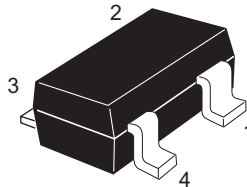
REJ03G0747-0200
(Previous ADE-208-746)
Rev.2.00
Aug.10.2005

Features

- Excellent inter modulation characteristic
- High power gain and low noise figure ;
PG=16dB typ. , NF=1.1dB typ. at f=900MHz

Outline

RENESAS Package code: PLSP0004ZA-A
(Package name: MPAK-4)



1. Collector
2. Emitter
3. Base
4. Emitter

Note: Marking is "ZS-".

Absolute Maximum Ratings

(Ta = 25°C)

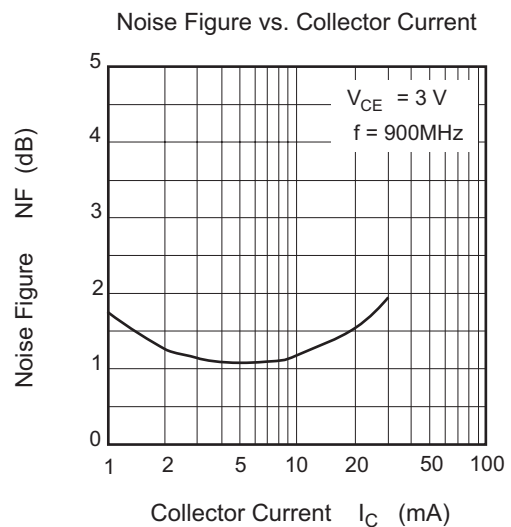
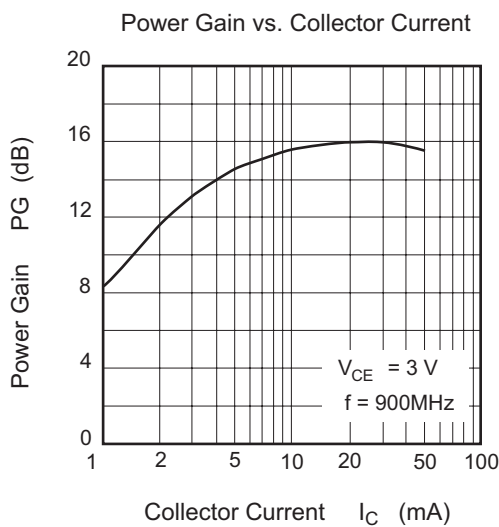
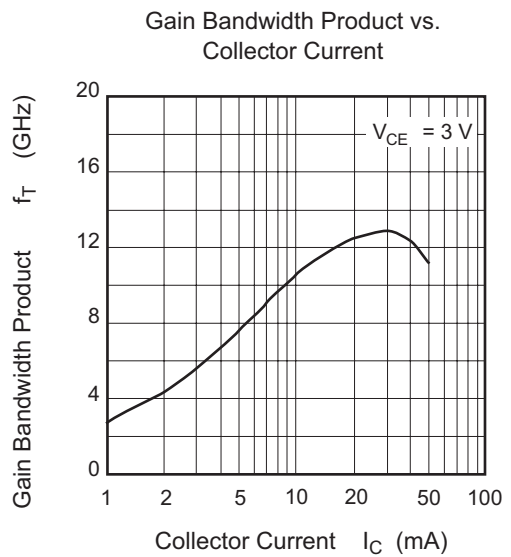
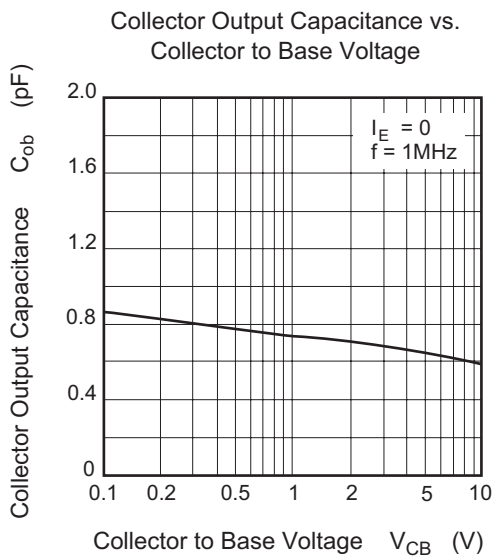
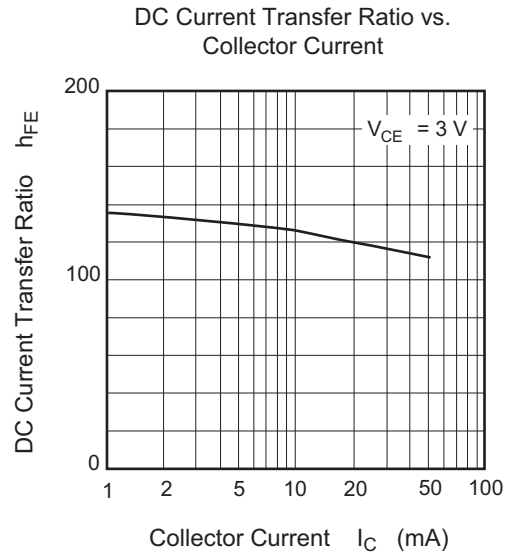
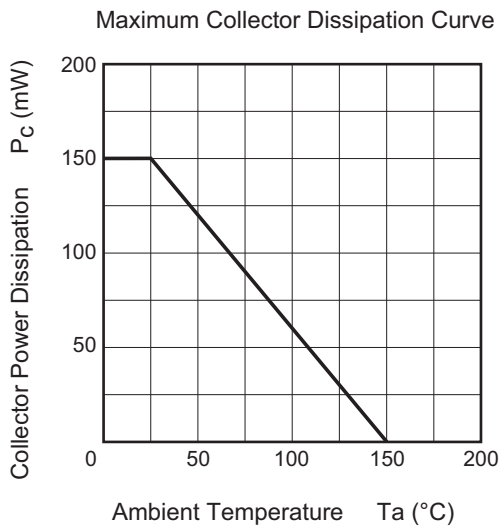
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	15	V
Collector to emitter voltage	V_{CEO}	6	V
Emitter to base voltage	V_{EBO}	1.5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

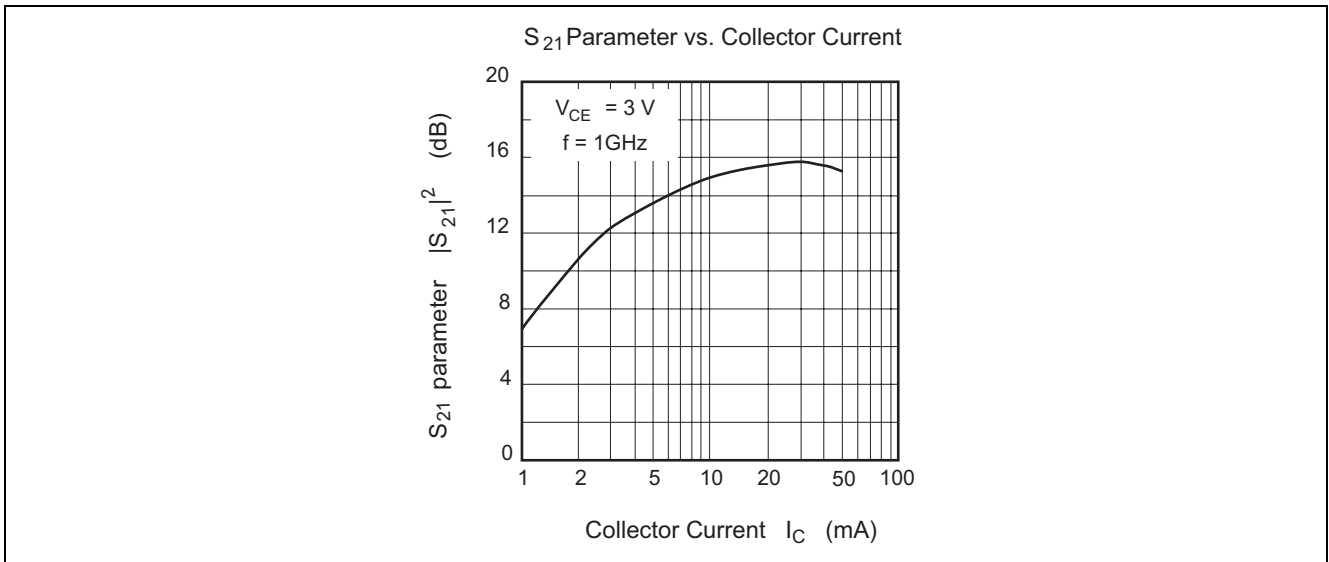
Electrical Characteristics

(Ta = 25°C)

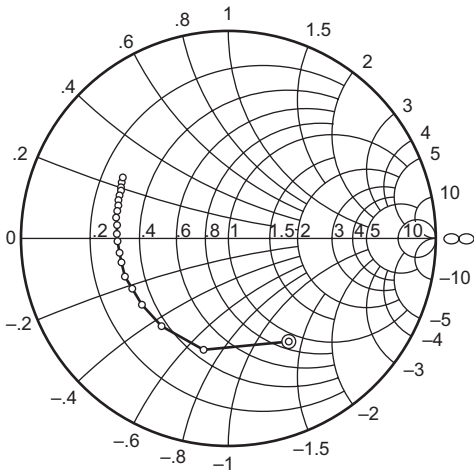
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	—	—	V	$I_C = 10\mu A, I_E = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 12V, I_E = 0$
Collector cutoff current	I_{CEO}	—	—	1	mA	$V_{CE} = 6V, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 1.5V, I_C = 0$
DC current transfer ratio	h_{FE}	80	120	160		$V_{CE} = 3V, I_C = 20mA$
Collector output capacitance	C_{ob}	—	0.69	1.1	pF	$V_{CB} = 3V, I_E = 0$ $f = 1MHz$
Gain bandwidth product	f_T	10	12.6	—	GHz	$V_{CE} = 3V, I_C = 20mA$
Power gain	PG	14	16	—	dB	$V_{CE} = 3V, I_C = 20mA$ $f = 900MHz$
Noise figure	NF	—	1.1	2.0	dB	$V_{CE} = 3V, I_C = 5mA$ $f = 900MHz$

Main Characteristics



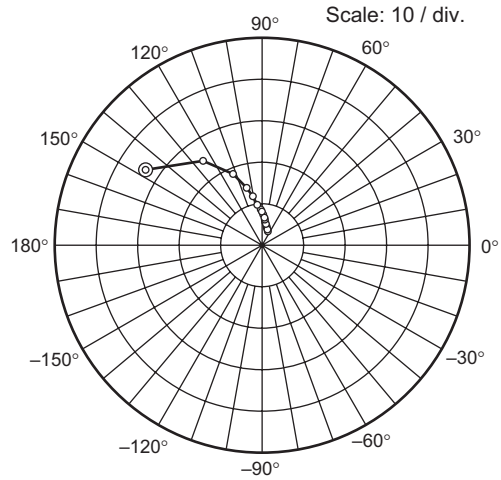


S11 Parameter vs. Frequency



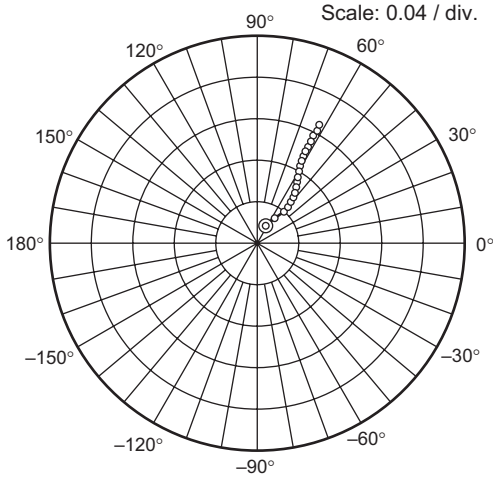
Condition : $V_{CE} = 3\text{ V}$, $I_C = 20\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙—○

S21 Parameter vs. Frequency



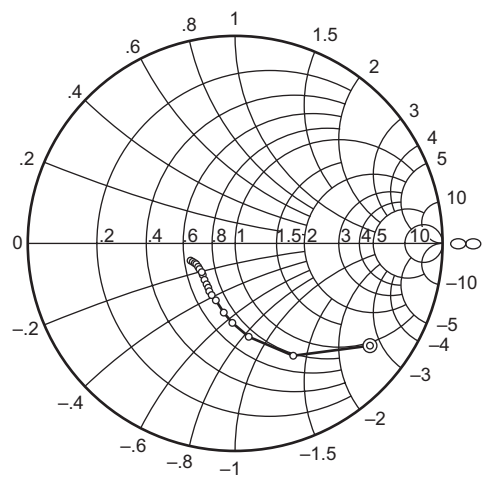
Condition : $V_{CE} = 3\text{ V}$, $I_C = 20\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙—○

S12 Parameter vs. Frequency



Condition : $V_{CE} = 3\text{ V}$, $I_C = 20\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙—○

S22 Parameter vs. Frequency



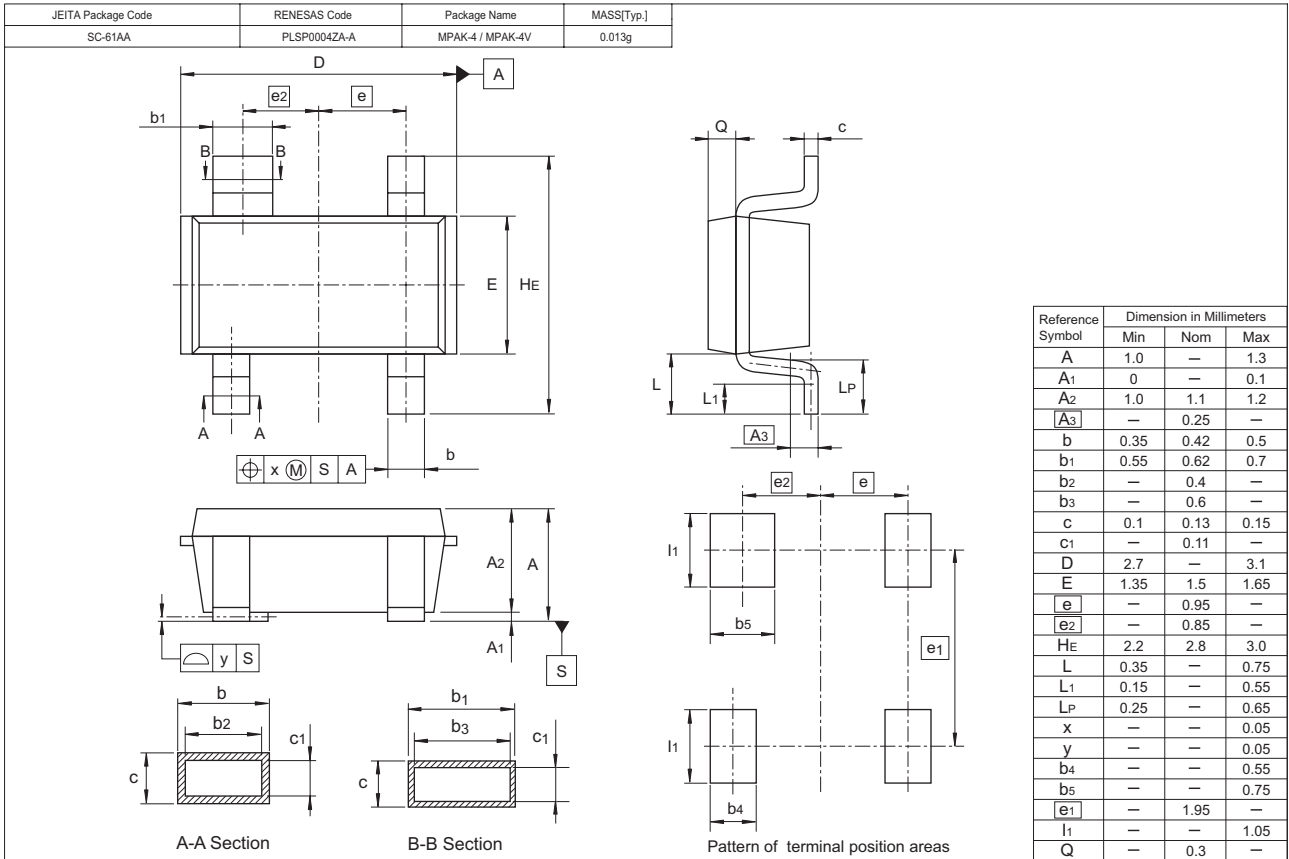
Condition : $V_{CE} = 3\text{ V}$, $I_C = 20\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙—○

Sparameter

 $(V_{CE} = 3V, I_C = 20mA, Z_o = 50\Omega)$

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.567	-60.8	34.04	146.8	0.0207	67.3	0.817	-37.3
200	0.539	-102.7	24.61	125.5	0.0329	54.3	0.605	-63.5
300	0.528	-128.1	18.16	113.2	0.0399	50.6	0.463	-80.5
400	0.525	-143.2	14.26	105.5	0.0447	50.3	0.379	-92.4
500	0.518	-153.6	11.65	100.2	0.0495	51.6	0.327	-101.8
600	0.526	-161.2	9.82	96.4	0.0545	53.3	0.293	-109.6
700	0.526	-167.9	8.48	92.9	0.0594	54.8	0.269	-116.2
800	0.528	-172.8	7.46	90.0	0.0639	56.1	0.253	-121.9
900	0.532	-178.3	6.63	87.4	0.0698	57.7	0.242	-127.0
1000	0.535	178.2	6.00	85.1	0.0741	58.7	0.235	-131.2
1100	0.536	174.2	5.48	82.9	0.0801	59.5	0.229	-135.1
1200	0.549	170.6	5.04	81.0	0.0851	60.6	0.225	-139.1
1300	0.546	167.6	4.67	79.1	0.0901	60.9	0.223	-142.0
1400	0.547	165.4	4.34	77.4	0.0961	61.5	0.222	-144.7
1500	0.552	162.4	4.09	75.7	0.102	62.1	0.222	-147.2
1600	0.562	159.4	3.82	74.0	0.106	62.3	0.223	-149.7
1700	0.561	157.3	3.62	72.5	0.113	62.5	0.224	-152.3
1800	0.563	154.8	3.43	70.7	0.118	62.9	0.227	-154.3
1900	0.573	152.5	3.26	69.2	0.124	62.3	0.229	-155.8
2000	0.577	150.0	3.13	67.8	0.130	63.0	0.232	-157.6

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC5545ZS-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

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